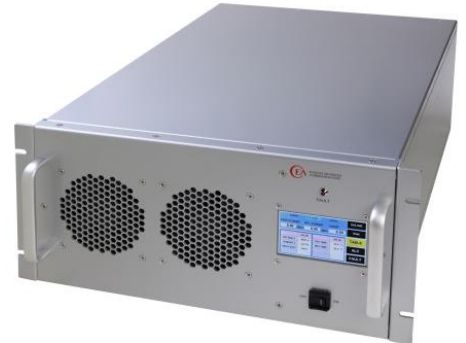




# AMP2012B SOLID STATE HIGH POWER AMPLIFIER

## FEATURES

- Rack mounted system
- Class AB linear LDMOS design
- Instantaneous RF & VHF band wide bandwidth coverage
- Designed for broadband EMI/RFI, Lab, Comm. and EW applications
- Suitable for all single channel modulation standards
- Built-in protection circuits
- High reliability and ruggedness



## ELECTRICAL SPECIFICATIONS: 50Ω, 25°C

Parameter	Specification	Notes
Operating Frequency Range	2 - 100 MHz	
Power Output	1000 Watt Min	CW
Power Gain	60 dB Min	
Power Gain Flatness	3.0 dB p-p Max	
Input Return Loss	-10 dB Max	Relative to 50 Ohm
2-Tone Intermodulation (IMD)	-25 dBc Typ	50dBm/Tone, Δ = 1MHz
Harmonics	2 <sup>nd</sup>	-30 dBc Typ
	3 <sup>rd</sup>	-15 dBc Typ
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	100 - 240 VAC	
Power Consumption	2600 Watt Max	At rated Pout
Input Power Protection	+8 dBm Max	<10 Sec without damage
Load VSWR Protection	5 : 1 Max	<1 minute at rated Pout

## ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Ambient Temperature	0 to +50 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

## MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions W x H x D	430 x 221 x 700 mm	5U
Weight	35 Kg. Max	
RF Connectors In/Out	Type-N Female	Front or rear panel
AC Power	IEC 60320-C14 / 9-Pin D-Sub	Or equivalent
Cooling	Built in Fan Cooling	Variable speed
Digital Monitor & Control FWD, REV, VSWR, GAIN, ALC, V & I, TEMP	Ethernet RJ-45 TCP/IP, RS422/485, USB Optional GPIB Interface	Optional Remote Bluetooth application

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## OUTLINE DRAWING

